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(54) Title of the Invention: **Antireflective hardmask composition and a method of preparing a patterned material using same**
Abstract Title: **Antireflective hardmask composition and a method of preparing a patterned material using same**

(57) An antireflective hardmask composition layer including a polymer having Si-O and non- silicon inorganic units in its backbone. The polymer includes chromophore and transparent moieties and a crosslinking component. The antireflective hardmask composition layer is employed in a method of forming a patterned material on a substrate.

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